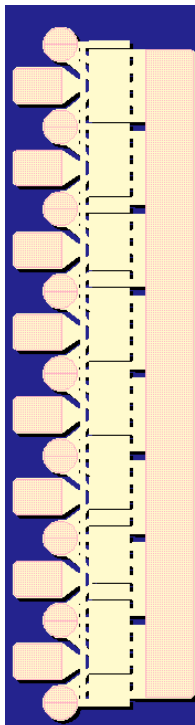


## 50 Watt Discrete Power GaN on SiC HEMT



### Key Features

- Frequency Range: DC - 18 GHz
- 47 dBm Nominal Psat
- 55% Maximum PAE
- 8.7 dB Nominal Power Gain
- Bias:  $V_d = 28 - 35$  V,  $I_{dq} = 1$  A,  $V_g = -3.6$  V Typical
- Technology: 0.25  $\mu$ m Power GaN on SiC
- Chip Dimensions: 0.82 x 2.48 x 0.10 mm

### Primary Applications

- Defense & Aerospace
- Broadband Wireless

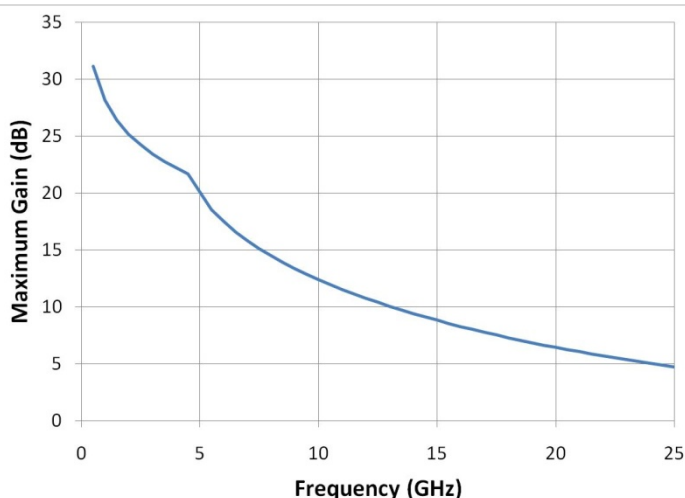
### Product Description

The TriQuint TGF2023-10 is a discrete 10 mm GaN on SiC HEMT which operates from DC-18 GHz. The TGF2023-10 is designed using TriQuint's proven 0.25 $\mu$ m GaN production process. This process features advanced field plate techniques to optimize microwave power and efficiency at high drain bias operating conditions.

The TGF2023-10 typically provides 47 dBm of saturated output power with power gain of 8.2 dB. The maximum power added efficiency is 55% which makes the TGF2023-10 appropriate for high efficiency applications.

Lead-free and RoHS compliant

Bias conditions:  $V_d = 30$  V,  $I_{dq} = 1$  A,  $V_g = -3.6$  V Typical



*Datasheet subject to change without notice.*

**Table I**  
**Absolute Maximum Ratings 1/**

Symbol	Parameter	Value	Notes
Vd	Drain Voltage	40 V	<u>2/</u>
Vg	Gate Voltage Range	-10 to 0 V	
Id	Drain Current	10 A	<u>2/</u>
Ig	Gate Current	56 mA	
Pin	Input Continuous Wave Power	40 dBm	<u>2/</u>
Tch	Channel Temperature	200 °C	

1/ These ratings represent the maximum operable values for this device. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device and / or affect device lifetime. These are stress ratings only, and functional operation of the device at these conditions is not implied.

2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed the maximum power dissipation listed in Table IV.

**Table II**  
**Recommended Operating Conditions**

Symbol	Parameter	Value
Vd	Drain Voltage	28 - 35 V
Idq	Drain Current	1 A
Id_Drive	Drain Current under RF Drive	3 A
Vg	Gate Voltage	-3.6 V

**Table III**  
**RF Characterization Table 1/**

**Bias: Vd = 30 V, Idq = 1000 mA, Vg = -3.6V Typical, Frequency = 10 GHz**

SYMBOL	PARAMETER	Vd = 30 V	UNITS
<b>Power Tuned:</b>			
Psat	Saturated Output Power	47	dBm
PAE	Power Added Efficiency	50	%
Gain	Power Gain	8.2	dB
$\Gamma_L$ 2/	Load Reflection Coefficient	0.92 $\angle$ 174	-
<b>Efficiency Tuned:</b>			
Psat	Saturated Output Power	46	dBm
PAE	Power Added Efficiency	55	%
Gain	Power Gain	8.7	dB
$\Gamma_L$ 2/	Load Reflection Coefficient	0.94 $\angle$ 172	-

SYMBOL	PARAMETER	Vd = 30 V	UNITS
<b>Power Tuned:</b>			
Rp 3/	Parallel Output Resistance	54.5	$\Omega$ ·mm
Cp 3/	Parallel Output Capacitance	0.376	pF/mm
<b>Efficiency Tuned:</b>			
Rp 3/	Parallel Output Resistance	86.0	$\Omega$ ·mm
Cp 3/	Parallel Output Capacitance	0.384	pF/mm

- 1/ Values in this table are scaled from measurements on a 1.25 mm GaN/SiC unit cell at 10 GHz
- 2/ Optimum  $\Gamma_L$  (Load) for maximum power or maximum PAE at 10 GHz, assuming all gates and drains are connected together
- 3/ Large signal equivalent output network (normalized) (see figure, pg 7)

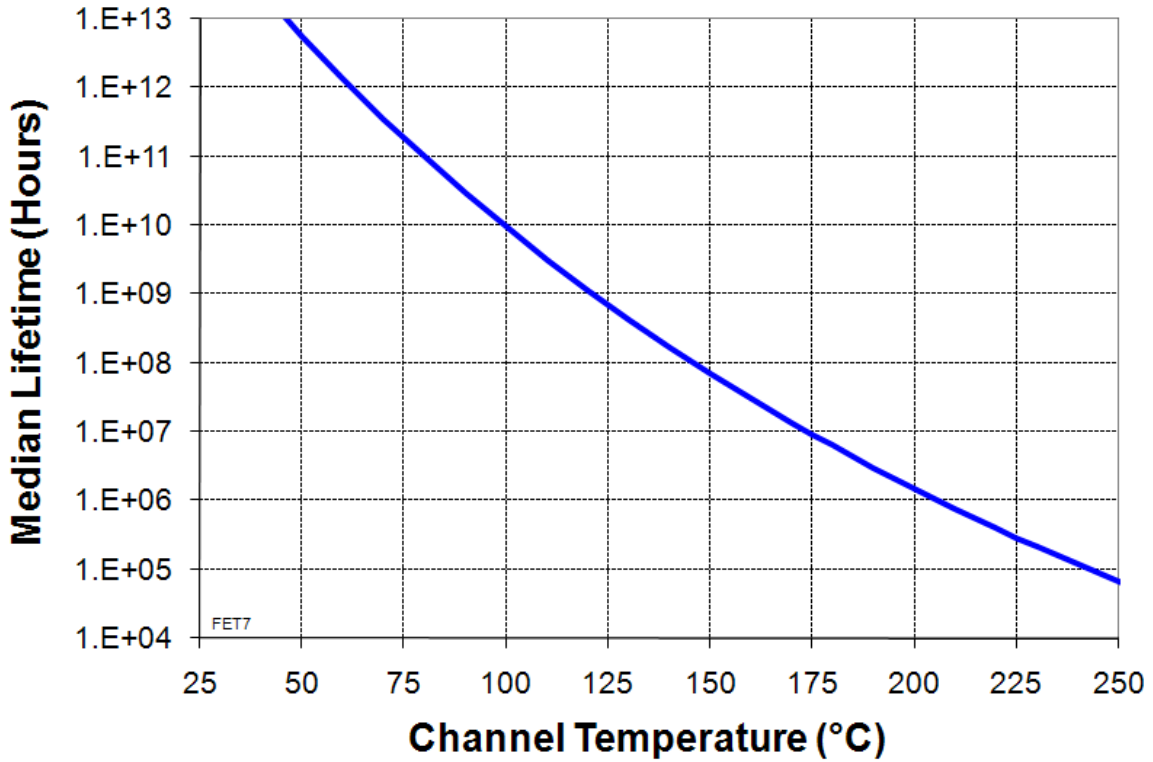
**Table IV**  
**Power Dissipation and Thermal Properties 1/**

Parameter	Test Conditions	Value	Notes
Maximum Power Dissipation	Tbaseplate = 70 °C	Pd = 64 W Tchannel = 200 °C Tm = 1.5E+6 Hrs	<u>2/</u>
Thermal Resistance, $\theta_{jc}$	Vd = 30 V Id = 1 A Pd = 30 W Tbaseplate = 70 °C	$\theta_{jc}$ = 2.0 (°C/W) Tchannel = 130 °C Tm = 4.4E+8 Hrs	
Thermal Resistance, $\theta_{jc}$ Under RF Drive	Vd = 30 V Id = 2.97 A Pout = 47 dBm Pd = 44.5 W Tbaseplate = 70 °C	$\theta_{jc}$ = 2.0 (°C/W) Tchannel = 160 °C Tm = 3.2E+7 Hrs	
Mounting Temperature	30 Seconds	320 °C	
Storage Temperature		-65 to 150 °C	

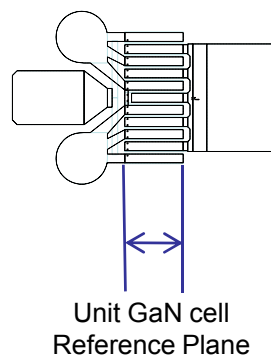
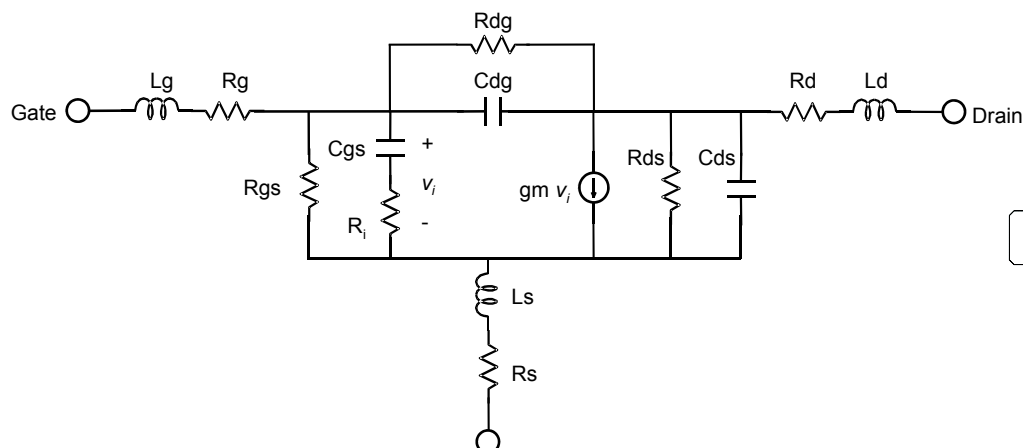
1/ Assumes eutectic attach using 1mil thick 80/20 AuSn mounted to a 10mil CuMo Carrier Plate

2/ Channel operating temperature will directly affect the device median lifetime. For maximum life, it is recommended that channel temperatures be maintained at the lowest possible levels.

### Median Lifetime vs Channel Temperature



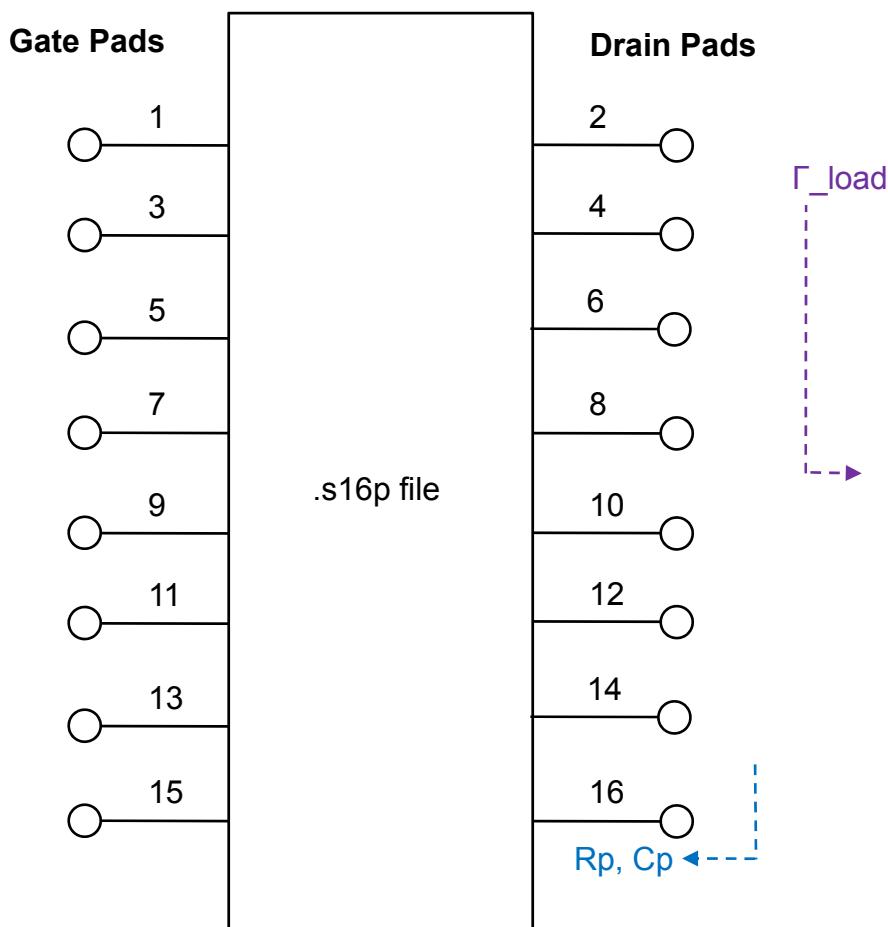
## Linear Model for 1.25 mm Unit GaN Cell (UGC)



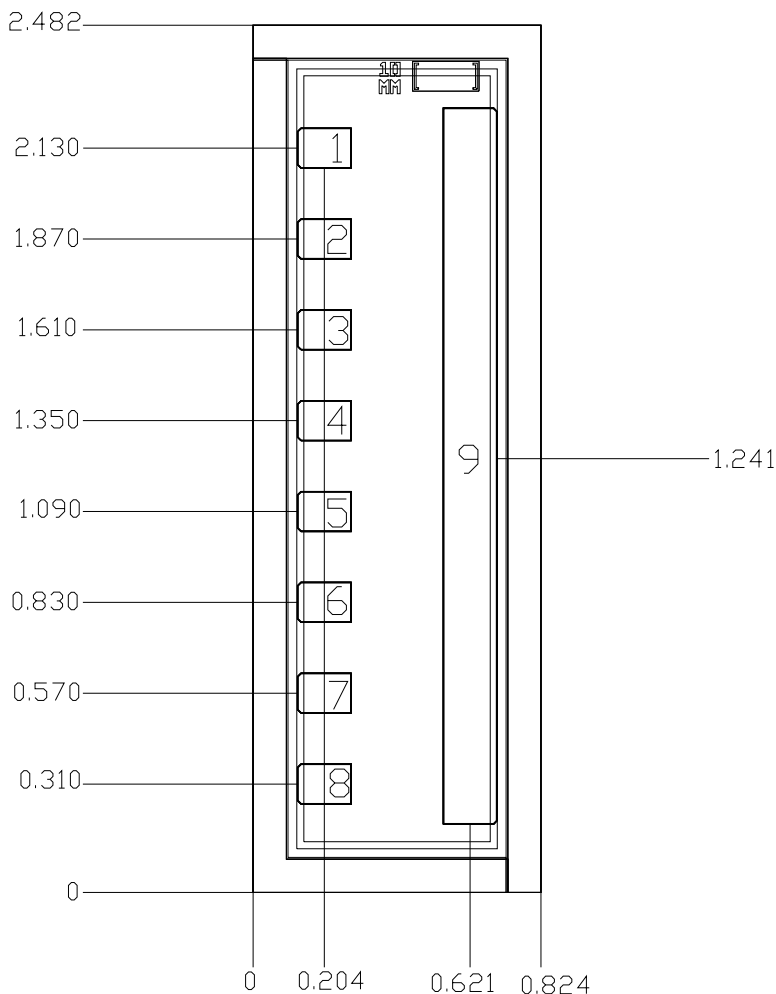
MODEL PARAMETER	Vd = 30V Idq = 125mA	UNITS
Rg	0.42	$\Omega$
Rs	0.13	$\Omega$
Rd	0.70	$\Omega$
gm	0.302	S
Cgs	1.994	pF
Ri	2.62	$\Omega$
Cds	0.275	pF
Rds	98.08	$\Omega$
Cgd	0.068	pF
Tau	0.19	pS
Ls	-0.002	nH
Lg	-0.026	nH
Ld	-0.017	nH
Rgs	37800	$\Omega$
Rgd	303000	$\Omega$

## Complete 10mm GaN HEMT Linear Model

Includes 8 UGC, 9 vias, and bonding pads



## Mechanical Drawing





## Assembly Notes

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment (i.e. epoxy) can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.

Reflow process assembly notes:

- Use AuSn (80/20) solder and limit exposure to temperatures above 300°C to 3-4 minutes, maximum.
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- Do not use any kind of flux.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Interconnect process assembly notes:

- Ball bonding is the preferred interconnect technique, except where noted on the assembly diagram.
- Force, time, and ultrasonics are critical bonding parameters.
- Aluminum wire should not be used.
- Devices with small pad sizes should be bonded with 0.0007-inch wire.

## Ordering Information

Part	ECCN	Package Style
TGF2023-10	3A001.b.3.b	GaN on SiC Die

***GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.***